Applied MDLx™ Ginestra™ Simulation Software

The Scientific Basis of Ginestra™ Physics

Recommended Methods to Study Resistive Switching Devices
Journal Advanced Electronic Materials, 5.1 (2019)

M. Lanza, Luca Larche, Andrea Padovani

The most recommended methodologies for the fabrication, characterization, and simulation of RS devices, and proper methods for displaying the data obtained.

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A Sensitivity Map-Based Approach to Profile Defects in MIM Capacitors From I – V , C – V , and G – V Measurements
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Andrea Padovani, Ben Kacze, Milan Pešić, Luca Larcher

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Understanding and Variability of Lateral Charge Migration in 3D CT-NAND Flash With and Without Band-Gap Engineered Barriers
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Andrea Padovani, Milan Pesic, Mondol Anik Kumar, Luca Larcher

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Milan Pešić, Luca Larcher

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